

# FFSB1065B-F085

## Silicon Carbide Schottky Diode

650 V, 10 A

### Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size & cost.

### Features

- Max Junction Temperature 175°C
- Avalanche Rated 49 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

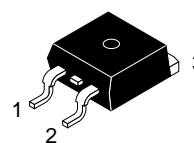
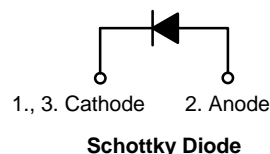
### Applications

- Automotive HEV-EV Onboard Chargers
- Automotive HEV-EV DC-DC Converters



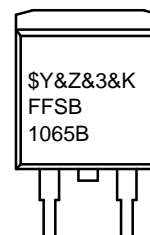
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D<sup>2</sup>PAK-3 (TO-263, 3-LEAD)  
CASE 418AJ

### MARKING DIAGRAM



|           |                         |
|-----------|-------------------------|
| \$Y       | = ON Semiconductor Logo |
| &Z        | = Assembly Plant Code   |
| &3        | = Numeric Date Code     |
| &K        | = Lot Code              |
| FFSB1065B | = Specific Device Code  |

### ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

# FFSB1065B–F085

## ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub> = 25°C unless otherwise noted)

| Symbol                            | Parameter   | Value                                    | Unit |   |
|-----------------------------------|---|--|------|---|
| V <sub>RRM</sub>                  | Peak Repetitive Reverse Voltage                               | 650                                      | V    |   |
| E <sub>AS</sub>                   | Single Pulse Avalanche Energy (Note 1)                        | 49                                       | mJ   |   |
| I <sub>F</sub>                    | Continuous Rectified Forward Current @ T <sub>C</sub> < 25°C  | 27                                       | A    |   |
|                                   | Continuous Rectified Forward Current @ T <sub>C</sub> < 146°C | 10                                       |      |   |
| I <sub>F, Max</sub>               | Non-Repetitive Peak Forward Surge Current                     | T <sub>C</sub> = 25°C, 10 μs             | 650  | A |
|                                   |   | T <sub>C</sub> = 150°C, 10 μs            | 570  | A |
| I <sub>F, SM</sub>                | Non-Repetitive Forward Surge Current<br>T <sub>C</sub> = 25°C | Half-Sine Pulse, t <sub>p</sub> = 8.3 ms | 45   | A |
| P <sub>tot</sub>                  | Power Dissipation   | T <sub>C</sub> = 25°C                    | 79   | W |
|                                   |   | T <sub>C</sub> = 150°C                   | 13   | W |
| T <sub>J</sub> , T <sub>STG</sub> | Operating and Storage Temperature Range                       | -55 to +175                              | °C   |   |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. E<sub>AS</sub> of 49 mJ is based on starting T<sub>J</sub> = 25°C, L = 0.5 mH, I<sub>AS</sub> = 14 A, V = 50 V.

## THERMAL CHARACTERISTICS

| Symbol           | Parameter                                 | Value | Unit |
|------------------|---|-------|------|
| R <sub>θJC</sub> | Thermal Resistance, Junction to Case, Max | 1.9   | °C/W |

## ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

| Symbol         | Parameter               | Test Condition                                 | Min | Typ  | Max | Unit |
|----------------|-------------------------|--|-----|------|-----|------|
| V <sub>F</sub> | Forward Voltage         | I <sub>F</sub> = 10 A, T <sub>C</sub> = 25°C   | –   | 1.38 | 1.7 | V    |
|                |                         | I <sub>F</sub> = 10 A, T <sub>C</sub> = 125°C  | –   | 1.6  | 2.0 |      |
|                |                         | I <sub>F</sub> = 10 A, T <sub>C</sub> = 175°C  | –   | 1.72 | 2.4 |      |
| I <sub>R</sub> | Reverse Current         | V <sub>R</sub> = 650 V, T <sub>C</sub> = 25°C  | –   | 0.5  | 40  | μA   |
|                |                         | V <sub>R</sub> = 650 V, T <sub>C</sub> = 125°C | –   | 1    | 80  |      |
|                |                         | V <sub>R</sub> = 650 V, T <sub>C</sub> = 175°C | –   | 2    | 160 |      |
| Q <sub>C</sub> | Total Capacitive Charge | V = 400 V                                      | –   | 25   | –   | nC   |
| C              | Total Capacitance       | V <sub>R</sub> = 1 V, f = 100 kHz              | –   | 421  | –   | pF   |
|                |                         | V <sub>R</sub> = 200 V, f = 100 kHz            | –   | 46   | –   |      |
|                |                         | V <sub>R</sub> = 400 V, f = 100 kHz            | –   | 35   | –   |      |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## ORDERING INFORMATION

| Part Number    | Top Marking | Package  | Shipping*         |
|----------------|-------------|--|-------------------|
| FFSB1065B–F085 | FFSB1065B   | D <sup>2</sup> PAK–3<br>(Pb-Free / Halogen Free) | 800 / Tape & Reel |

\* For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D

TYPICAL CHARACTERISTICS

( $T_J = 25^\circ\text{C}$  unless otherwise noted)

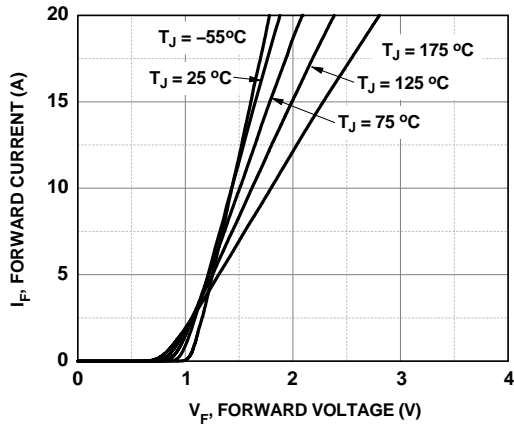


Figure 1. Forward Characteristics

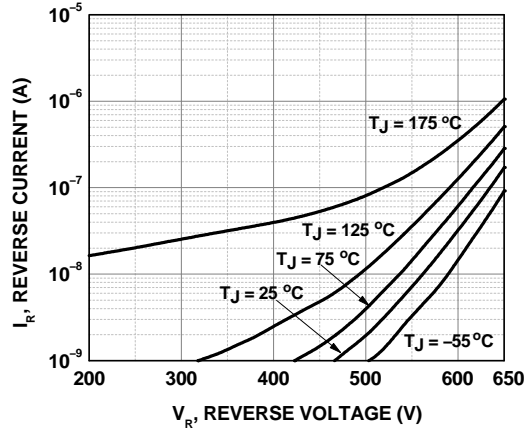


Figure 2. Reverse Characteristics

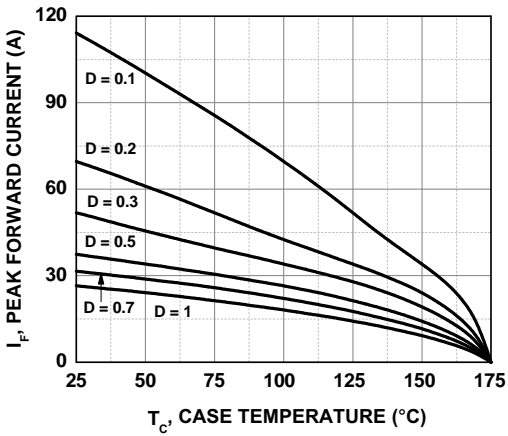


Figure 3. Current Derating

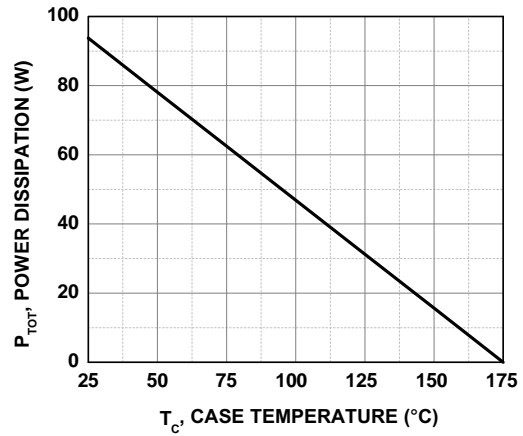


Figure 4. Power Derating

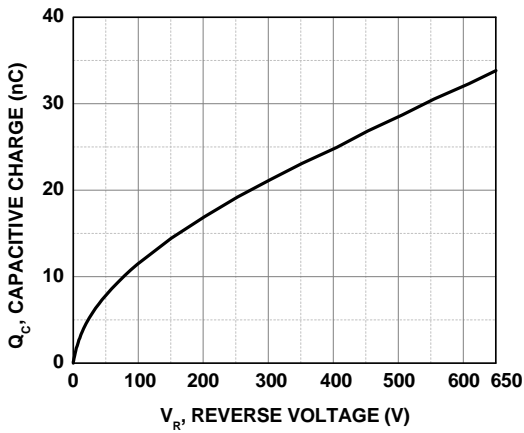


Figure 5. Capacitive Charge vs. Reverse Voltage

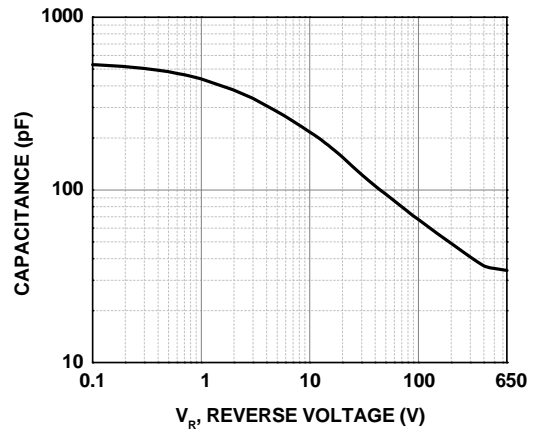


Figure 6. Capacitance vs. Reverse Voltage

# FFSB1065B-F085

## TYPICAL CHARACTERISTICS

( $T_J = 25^\circ\text{C}$  unless otherwise noted)

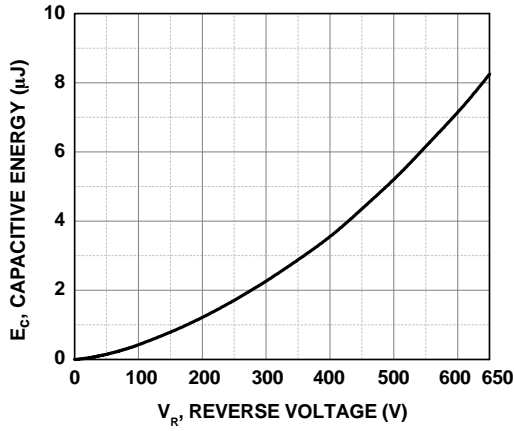


Figure 7. Capacitance Stored Energy

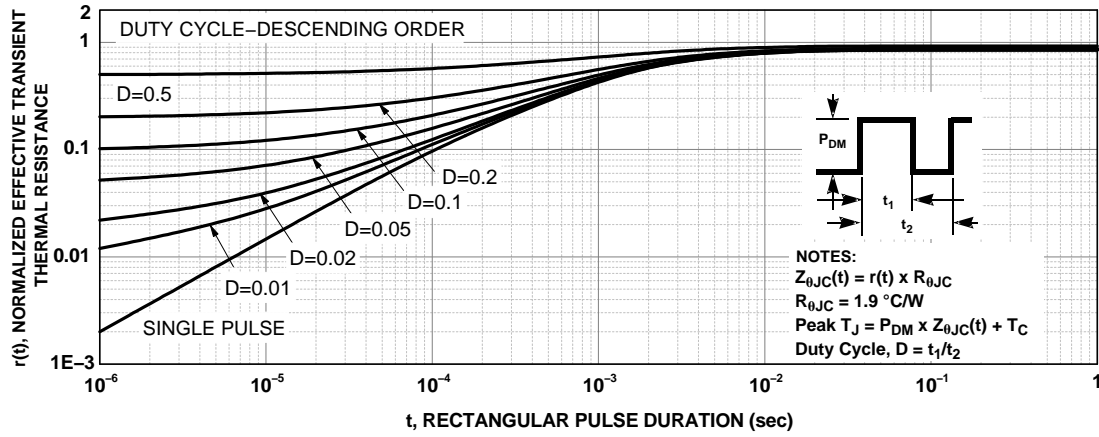


Figure 8. Junction-to-Case Transient Thermal Response Curve

# FFSB1065B-F085

## TEST CIRCUIT AND WAVEFORMS

$L = 0.5 \text{ mH}$   
 $R < 0.1 \Omega$   
 $V_{DD} = 50 \text{ V}$   
 $E_{AVL} = 1/2LI^2 [V_{R(AVL)} / (V_{R(AVL)} - V_{DD})]$   
 $Q1 = \text{IGBT (} BV_{CES} > \text{DUT } V_{R(AVL)} \text{)}$

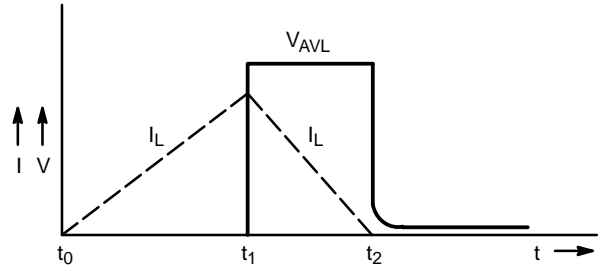
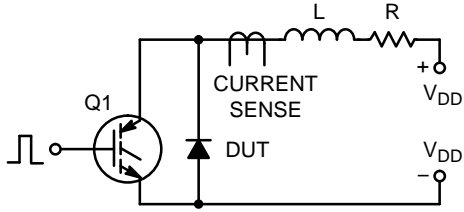
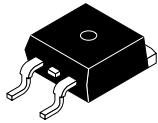


Figure 9. Unclamped Inductive Switching Test Circuit & Waveform

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

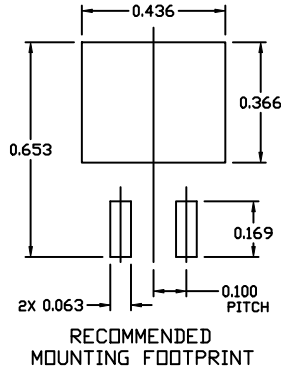
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DATE 13 AUG 2019

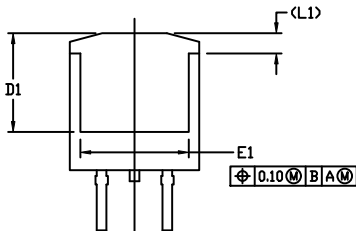
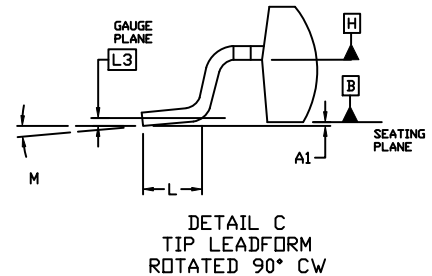
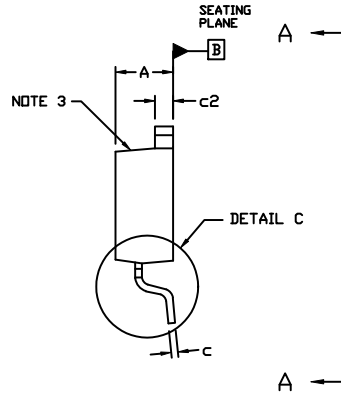
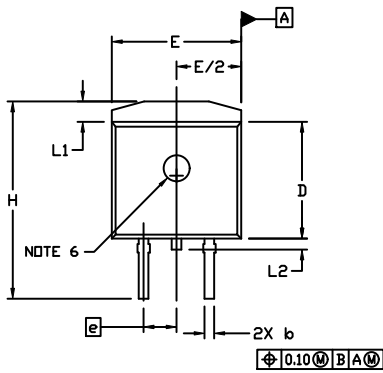
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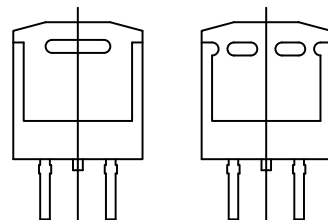
**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES
3. CHAMFER OPTIONAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.005 PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.
5. THERMAL PAD CONTOUR IS OPTIONAL WITHIN DIMENSIONS E, L1, D1, AND E1.
6. OPTIONAL MOLD FEATURE.

| DIM | INCHES |       | MILLIMETERS |       |
|-----|--------|-------|-------------|-------|
|     | MIN.   | MAX.  | MIN.        | MAX.  |
| A   | 0.160  | 0.190 | 4.06        | 4.83  |
| A1  | 0.000  | 0.010 | 0.00        | 0.25  |
| b   | 0.020  | 0.039 | 0.51        | 0.99  |
| c   | 0.012  | 0.029 | 0.30        | 0.74  |
| c2  | 0.045  | 0.065 | 1.14        | 1.65  |
| D   | 0.330  | 0.380 | 8.38        | 9.65  |
| D1  | 0.260  | ---   | 6.60        | ---   |
| E   | 0.380  | 0.420 | 9.65        | 10.67 |
| E1  | 0.245  | ---   | 6.22        | ---   |
| e   | 0.100  | BSC   | 2.54        | BSC   |
| H   | 0.575  | 0.625 | 14.60       | 15.88 |
| L   | 0.070  | 0.110 | 1.78        | 2.79  |
| L1  | ---    | 0.066 | ---         | 1.68  |
| L2  | ---    | 0.070 | ---         | 1.78  |
| L3  | 0.010  | BSC   | 0.25        | BSC   |
| M   | -8°    | 8°    | -8°         | 8°    |

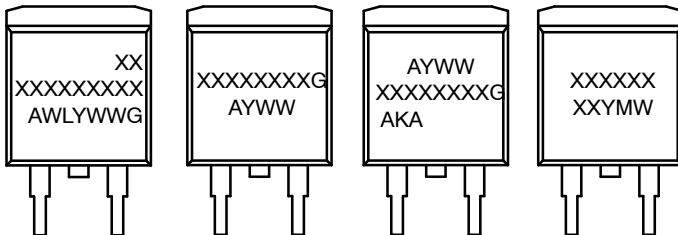


VIEW A-A



VIEW A-A  
OPTIONAL CONSTRUCTIONS

**GENERIC MARKING DIAGRAMS\***



IC

Standard

Rectifier

SSG

- XXXXXX = Specific Device Code
- A = Assembly Location
- WL = Wafer Lot
- Y = Year
- WW = Work Week
- W = Week Code (SSG)
- M = Month Code (SSG)
- G = Pb-Free Package
- AKA = Polarity Indicator

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

|                         |  |  |
|-------------------------|--|--|
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| <b>DESCRIPTION:</b>     | <b>D<sup>2</sup>PAK-3 (TO-263, 3-LEAD)</b> | <b>PAGE 1 OF 1</b>   |

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